
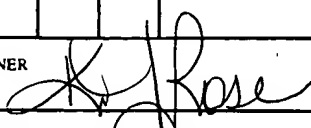
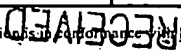
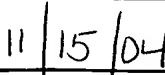
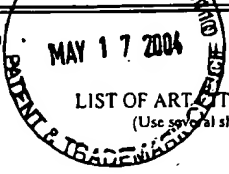
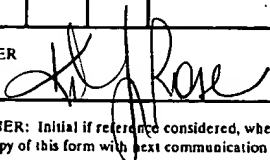


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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Vishnu K. Agarwal et al.			
FILING DATE October 26, 1999				GROUP 2822			
PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
RR	AA	5,973,911	10-1999	Nishioka			
RR	AB	6,727,143 B1	04-2004	Hui et al.			
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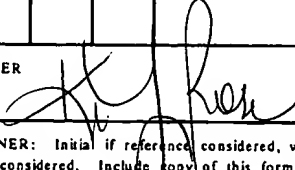
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		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)						APPLICANT Vishnu K. Agarwal et al.	
								FILING DATE October 26, 1999	
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KR	AA	5,920,775	07-1999	Kob					
KR	AB	6,376,332 B1	04-2002	Yanagita et al.					
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<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>									

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)						APPLICANT Vishnu K. Agarwal et al.			
						FILING DATE October 26, 1999		GROUP 2822	
U.S. PATENT DOCUMENTS									
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KL	AA	6,204,203 B1	03-2001	Narwankar et al.					
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FOREIGN PATENT DOCUMENTS									
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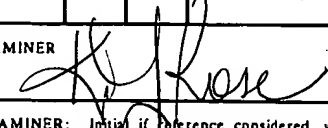
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<b>LIST OF ART CITED BY APPLICANT</b> (Use several sheets if necessary)					APPLICANT VISHNU K. AGARWAL ET AL.			
					FILING DATE APRIL 10, 1998		GROUP 2822	
U.S. PATENT DOCUMENTS								
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KR	AA	09/033,063	AL-SHAREEF ET AL.			02/28/1998		
	AB	09/033,064	AL-SHAREEF ET AL.			02/28/1998		
	AC	09/058,612	AGARWAL ET AL.			04/10/1998		
	AD	09/083,257	AL-SHAREEF ET AL.			05/21/1998		
	AE	09/137,780	AL-SHAREEF ET AL.			08/20/1998		
	AF	09/074,638	AGARWAL ET AL.			05/07/1998		
	AG	08/858,027	SANDHU ET AL.			05/16/1997		
	AH	08/881,561	SANDHU ET AL.			06/24/1997		
	AI	09/086,389	SANDHU ET AL.			05/28/1998		
	AJ	09/122,473	SCHUEGRAF			07/23/1998		
KR	AK	09/098,035	DeBOER ET AL.			06/15/1998		
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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RR	AA	09/185,412		GRAETTINGER ET AL.			11/03/1998
	AB	09/229,518		DeBOER ET AL.			01/13/99
	AC	08/994,054		PAREKH ET AL.			08/97
	AD	08/670,644		GRAETTINGER ET AL.			
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RR	AA	5,930,584	07/99	SUN ET AL.			
	AB	5,910,218	06/99	PARK ET AL.			
	AC	5,279,985	01/1994	KAMIYAMA	437	60	
	AD	5,335,138	08/1994	SANDHU ET AL.	361	303	
	AE	5,372,859	12/1994	THAKOOR	427	551	
	AF	5,466,629	11/1995	MIHARA ET AL.	437	60	
	AG	5,510,651	04/1996	MANIAR ET AL.	257	751	
	AH	5,555,486	09/1996	KINGON ET AL.	361	305	
	AI	5,814,852	09/1998	SANDHU ET AL.	257	310	
	AJ	5,844,771	12/1998	GRAETTINGER ET AL.	361	303	
RR	AK	4,891,682	01/1990	YUSA ET AL.	357	30	
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RR	AL	1-222469 A	05/1989	JAPAN			
RR	AM	06-021333	01/1994	JAPAN (Kato)			Abs.
RR	AN	05-221644	08/1993	JAPAN (Munichiro et al.)			Abs.
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RR	AR	McINTYRE, Paul C. et al., <i>Kinetics and Mechanisms of TiN Oxidation Beneath Pt/TiN Films</i> , J. Appl. Phys., Vol. 82, No. 9, pp. 4577-4585 (11/1997).					
	AS	LESAICHERRE, P-Y et al., <i>A Gbit-Scale DRAM Stacked Capacitor Technology with ECR MOCVD SrTiO<sub>3</sub> and RIE Patterned RuO<sub>2</sub>/TiN Storage Nodes</i> , 1994 IEEE, pp. 831-834.					
RR	AT	ONISHI, Shigeo et al., <i>A Half-Micron Ferroelectric Memory Cell Technology With Stacked Capacitor Structure</i> , 1994 IEEE, IDEN 94-843, pp. 843-846.					
EXAMINER <i>H. Rose</i>				DATE CONSIDERED 11/15/04			
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KR 	AA	5,079,191	01/1992	SHINRIKI ET AL.		
	AB	5,142,438	08/1992	REINBERG ET AL.		
	AC	5,234,556	08/1993	OISHI ET AL.		
	AD	5,316,982	05/1994	TANIGUCHI		
	AE	5,330,935	07/1994	DOBUZINSKY ET AL.		
	AF	5,352,623	10/1994	KAMIYAMA		
	AG	5,362,632	11/1994	MATHEWS		
	AH	5,468,687	11/1995	CARL ET AL.		
	AI	5,688,724	11/1997	YOON ET AL.		
	AJ	5,552,337	09/1996	KWON ET AL.		
KR	AK	5,348,894	09/1994	GNADÉ ET AL.		
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	AP					
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
KR 	AR		KAMIYAMA, S. et al., <i>Ultrathin Tantalum Oxide Capacitor Dielectric Layers Fabricated Using Rapid Thermal Nitradation Prior to Low Pressure Chemical Vapor Deposition</i> , J. Electrochem. Soc., Vol 140, No. 6, June 1993, pp. 1617-1625.			
	AS		EIMORI, T. et al., <i>A Newly Designed Planar Stacked Capacitor Cell with High Dielectric Constant Film for 256Mbit Dram</i> , 1993 IEEE, pp. 631-634.			
KR	AT		YAMAGUCHI, H. et al., <i>Structural and Electrical Characterization of SrTiO<sub>3</sub> Thin Films Prepared by Metal Organic Chemical Vapor Deposition</i> , Jpn. J. appl. Phys., Vol. 32, 1993, Pt. 1, No. 9B, pp. 4069-4073.			
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT VISHNU K. ACARWAL ET AL.	
				FILING DATE APRIL 10, 1998	GROUP 2822

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RR	AA	4,952,904	08/1990	JOHNSON ET AL.			
	AB	5,798,903	08/1998	DHOTE ET AL.			
	AC	5,790,366	08/1998	DESU ET AL.			
	AD	5,561,307	10/1996	MIHARA ET AL.			
	AE	5,508,953	04/1996	FUKUDA ET AL.			
	AF	5,293,510	03/1994	TAKENAKA			
	AG	5,191,510	03/1993	HUFFMAN			
	AH	5,053,917	10/1991	MIYASAKA ET AL.			
	AI	5,843,830	12/1998	GRAETTINGER ET AL.			
	AJ	5,838,035	11/1998	RAMESH			
RR	AK	5,837,593	11/1998	PARK ET AL.			

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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)			
RR	AR	FAZAN, P.C. et al., <i>A High-C Capacitor (20.4fF/μm<sup>2</sup>) with Ultrathin CVD-Ta<sub>2</sub>O<sub>5</sub> Films Deposited on Rugged Poly-Si for High Density DRAMs</i> , 1992 IEEE, pp. 263-266.	
	AS	KAMIYAMA, S., et. al., <i>Highly Reliable 2.5um Ta<sub>2</sub>O<sub>5</sub> Capacitor Process Technology for 256Mbit DRAMs</i> , 1991 IEEE, pp. 827-830.	
RR	AT	FAROOQ, M.A. et al., <i>Tantalum nitride as a diffusion barrier between Pd<sub>3</sub>Si, CoSi<sub>2</sub> and aluminum</i> , 1989 American Institute of Physics, pp. 3017-3022.	

EXAMINER <i>[Signature]</i>	DATE CONSIDERED 11/15/04
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	AB	5,780,359	07/1998	BROWN ET AL.			
	AC	5,728,603	03/1998	EMESH ET AL.			
	AD	5,504,041	04/1996	SUMMERFELT			
	AE	5,471,364	11/1995	SUMMERFELT ET AL.			
	AF	5,654,222	08/1997	SANDHU ET AL.			
	AG	5,663,088	09/1997	SANDHU ET AL.			
	AH	5,442,213	08/1995	OKUDAIRA			
	AI	4,464,701	08/1984	ROBERTS ET AL.			
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
<div style="font-size: 2em; font-family: cursive;">KR</div>	AR	S. Wolf and R.N. Tauber, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Lattice Press, pages 589-591.					
<div style="font-size: 2em; font-family: cursive;">KR</div>	AS	Anonymous Research Disclosure, 1989RD-0299041 titled <i>Double High Dielectric Capacitor</i> , Derwent-Week 198917					
		(Derwent World Patent Index).					
	AT						
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